



#### **40V NPN SMALL SIGNAL TRANSISTOR IN DFN1006**

#### Features

- BV<sub>CEO</sub> > 40V
- I<sub>C</sub> = 200mA High Collector Current
- P<sub>D</sub> = 1000mW Power Dissipation
- 0.60mm<sup>2</sup> Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type MMBT3906LP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

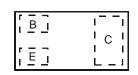
#### **Mechanical Data**

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
  Terminals: Finish NiPdAu.
- Solderable per MIL-STD-202, Method 208 @
- Weight: 0.0008 grams (Approximate)

X1-DFN1006-3

Bottom View

Device Symbol



Top View Device Schematic

#### Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3904LP-7	1N	7	8mm	3,000
MMBT3904LP-7B	1N	7	8mm	10,000

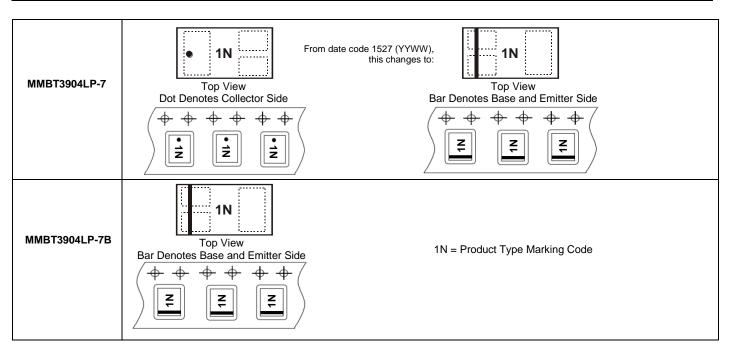
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com.

#### **Marking Information**





## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	lc	200	mA
Peak Collector Current	I <sub>CM</sub>	200	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	P	400	mW	
	(Note 6)		1000	TIVV	
Thermal Registeres, Junction to Ambient	(Note 5)		310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	120		
Thermal Resistance, Junction to Lead	(Note 7)	R <sub>θJL</sub>	120	°C/W	
Operating and Storage and Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes: 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.

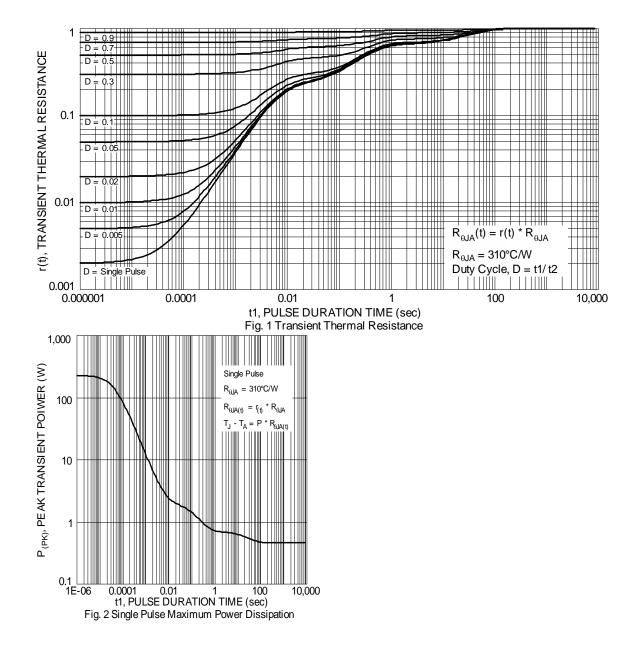
6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.

7. Thermal resistance from junction to solder-point (on the exposed collector pad).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



#### **Thermal Characteristics**





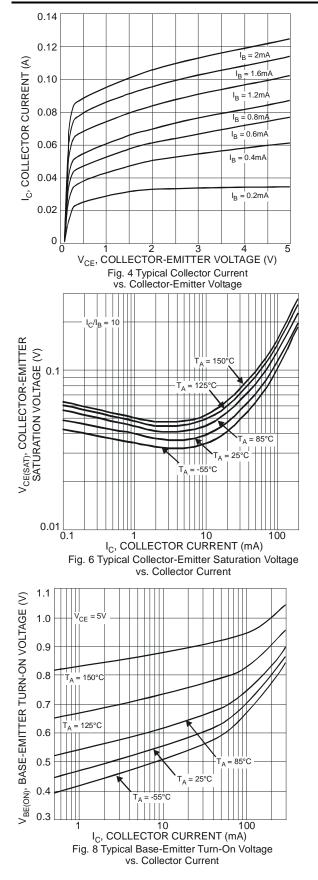
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

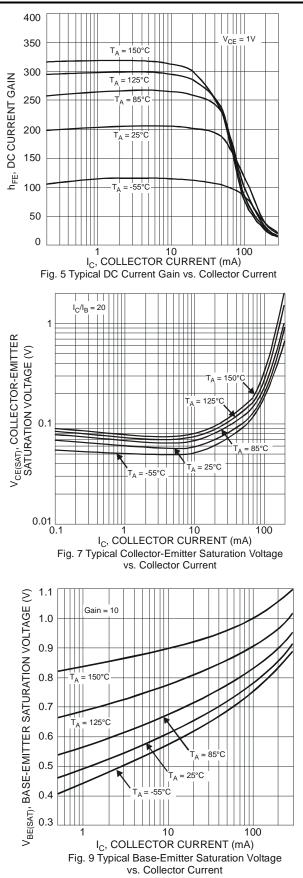
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS	<b>cjci</b>			•	
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	—	V	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	40	—	V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	—	V	$I_{E} = 10\mu A, I_{C} = 0$
Collector Cutoff Current	ICEX		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
Base Cutoff Current	I <sub>BL</sub>		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
ON CHARACTERISTICS (Note 9)					
		40	—		$I_{C} = 100 \mu A, V_{CE} = 1.0 V$
		70	—		$I_{C} = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	100	300	—	$I_{C} = 10 \text{mA}, V_{CE} = 1.0 \text{V}$
		60	—		$I_{C} = 50 \text{mA}, V_{CE} = 1.0 \text{V}$
		30	_		$I_{C} = 100 \text{mA}, V_{CE} = 1.0 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	0.20		$I_{C} = 10mA$ , $I_{B} = 1.0mA$
	V CE(sat)		0.30		$I_{C} = 50 \text{mA}, I_{B} = 5.0 \text{mA}$
Base-Emitter Saturation Voltage	V	0.65	0.85 V	$I_{C} = 10 \text{mA}, I_{B} = 1.0 \text{mA}$	
Dase-Emilier Saturation Voltage	V <sub>BE(sat)</sub>	_	0.95	v	$I_{C} = 50 \text{mA}, I_{B} = 5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS				•	
Output Capacitance	C <sub>obo</sub>		4.0	pF	$V_{CB} = 5.0V, f = 1.0MHz, I_E = 0$
Input Capacitance	Cibo		8.5	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h <sub>fe</sub>	100	400	—	f = 1.0kHz
Output Admittance	h <sub>oe</sub>	1.0	40	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	_	MHz	$V_{CE} = 20V, I_C = 10mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>		35	ns	$V_{CC} = 3.0V, I_C = 10mA,$
Rise Time	tr	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	t <sub>f</sub>		50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



#### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

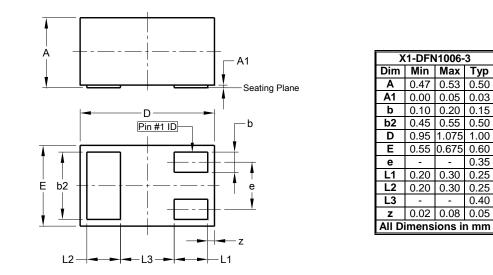






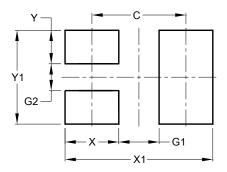
### **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70

0.15

0.50

1.00

0.60 0.35

0.25

0.25

0.40



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